

28. A method according to claim 27, said method further comprising:  
disposing a transparent electrode comprising gold on the second clad layer; and  
disposing an electrode pad on the first clad layer.

Control  
B<sup>2</sup>  
29. (Amended) A method according to claim 27, said method further comprising:  
interposing a layer comprising  $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}$  (including  $X=0$ ,  $Y=0$ ,  $X=Y=0$ ) between  
the light emitting layer and the second clad layer,  
wherein said interposed layer has a wide band gap and is doped with an acceptor.

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B<sup>3</sup>  
32. (Amended) A method according to claim 27, said method further comprising:  
growing the layers as crystals by a metal organic vapor phase epitaxial growth  
method with nitrogen, ammonia and alkyl compound gases containing a group III element.

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**Please see the attached Appendix for the changes made to effect the above claims.**